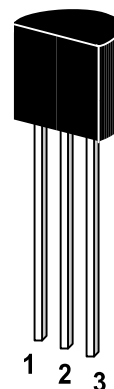


ST 2SC3202

NPN Silicon Epitaxial Planar Transistor
for switching and general purpose applications.

The transistor is subdivided into two groups, O and Y
according to its DC current gain.

On special request, these transistors can be
manufactured in different pin configurations.



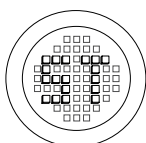
1. Emitter 2. Collector 3. Base

TO-92 Plastic Package
Weight approx. 0.19g

Absolute Maximum Ratings ($T_a = 25^{\circ}\text{C}$)

	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	35	V
Collector Emitter Voltage	V_{CEO}	30	V
Emitter Base Voltage	V_{EBO}	5	V
Collector Current	I_C	500	mA
Emitter Current	I_E	-500	mA
Power Dissipation	P_{tot}	625	mW
Junction Temperature	T_j	150	$^{\circ}\text{C}$
Storage Temperature Range	T_s	-55 to +150	$^{\circ}\text{C}$

G S P FORM A IS AVAILABLE



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РАДИОТЕХ

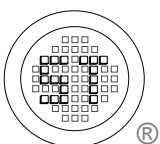
Тел.: (495) 795-0805
Факс: (495) 234-1603
Эл. почта: info@rct.ru
Веб: www.rct.ru

ST 2SC3202

Characteristics at $T_{amb}=25\text{ }^{\circ}\text{C}$

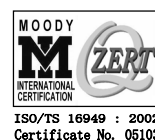
	Symbol	Min.	Typ.	Max.	Unit		
DC Current Gain at $V_{CE}=1\text{V}$, $I_C=100\text{mA}$ Current Gain Group	O	h_{FE}	70	-	140	-	
	Y	h_{FE}	120	-	240	-	
	at $V_{CE}=6\text{V}$, $I_C=400\text{mA}$	O	h_{FE}	25	-	--	--
		Y	h_{FE}	40	-	-	-
Collector Cutoff Current at $V_{CB}=35\text{V}$	I_{CBO}	-	-	0.1	μA		
Emitter Cutoff Current at $V_{EB}=5\text{V}$	I_{EBO}	-	-	0.1	μA		
Collector Emitter Saturation Voltage at $I_C=100\text{mA}$, $I_B=10\text{mA}$	$V_{CE(sat)}$	-	0.1	0.25	V		
Base Emitter Voltage at $V_{CE}=1\text{V}$, $I_C=100\text{mA}$	V_{BE}	-	0.8	1	V		
Transition Frequency at $V_{CE}=6\text{V}$, $I_C=20\text{mA}$	f_T	-	300	-	MHz		
Collector Output Capacitance at $V_{CB}=6\text{V}$, $f=1\text{MHz}$	C_{OB}	-	7.0	-	pF		

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SEMTECH ELECTRONICS LTD.

(Subsidiary of Semtech International Holdings Limited, acompany
listed on the Hong Kong Stock Exchange, Stock Code: 724)



ISO/TS 16949 : 2002
Certificate No. 05103



ISO 14001
Certificate No. 7116



ISO 9001 : 2000
Certificate No. 0001-1999-01-002-001

Dated : 07/12/2002